



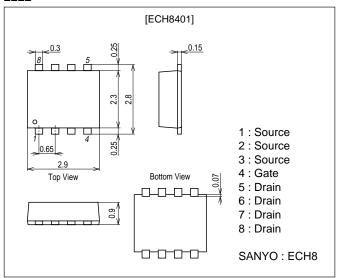
Ultrahigh-Speed Switching Applications

Features

- · Low ON-resistance.
- · Ultrahigh-speed switching.
- · 2.5V drive.

Package Dimensions

unit : mm 2222



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		20	V
Gate-to-Source Voltage	VGSS		±12	V
Drain Current (DC)	ID		10	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	40	Α
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm ² X0.8mm)	1.6	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	01111
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0	20			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0			±10	μΑ
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	0.5		1.3	V

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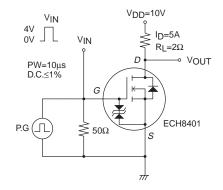
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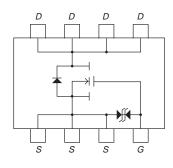
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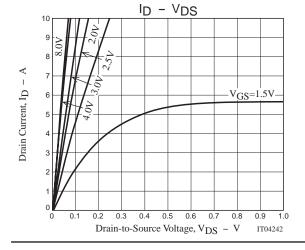
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =5A	14	20		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =5A, V _{GS} =4V		9	14	mΩ
	RDS(on)2	ID=5A, VGS=3.1V		10	15.5	mΩ
	R _{DS} (on)3	I _D =2A, V _{GS} =2.5V		12	19	mΩ
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		1700		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		330		pF
Reverse Transfer Capacitance	Crss	V _{DS} =10V, f=1MHz		270		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit		29		ns
Rise Time	t _r	See specified Test Circuit		150		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		220		ns
Fall Time	t _f	See specified Test Circuit		160		ns
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =10V, I _D =5A		52		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =10V, I _D =5A		2.6		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =10V, I _D =5A		7.4		nC
Diode Forward Voltage	VsD	IS=10A, VGS=0		0.82	1.2	V

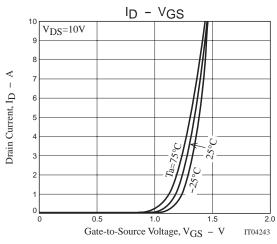
Switching Time Test Circuit



Electrical Connection

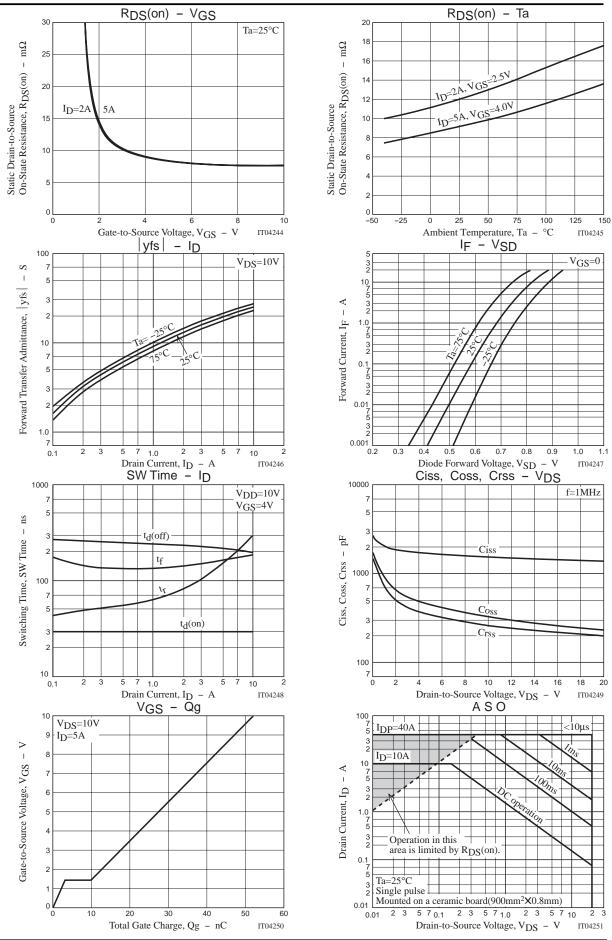


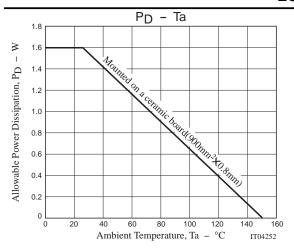




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